

MA81

Silicon epitaxial planer type

For band switching

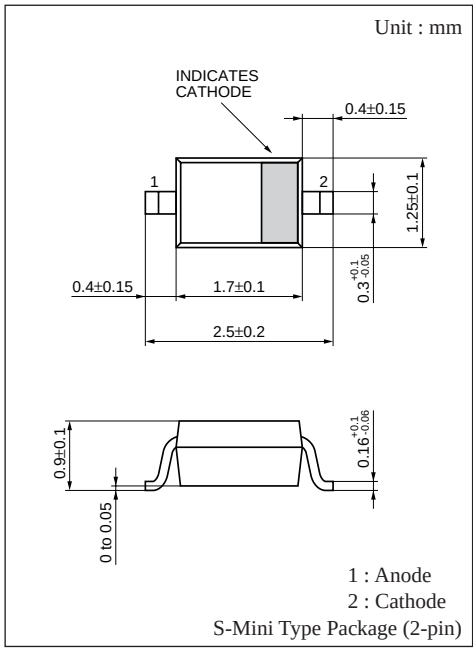
■ Features

- S-Mini package, enabling down-sizing of the equipment and automatic insertion through taping
- Small diode capacity C_D
- Low forward dynamic resistance r_f
- Optimum for a band switching of tuner

■ Absolute Maximum Ratings (Ta= 25°C)

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	35	V
Forward current (DC)	I_F	100	mA
Operating ambient temperature	T_{opr}^*	− 25 to + 85	°C
Storage temperature	T_{stg}	− 55 to +150	°C

* Maximum ambient temperature during operation



Marking Symbol : 4D

■ Electrical Characteristics (Ta= 25°C)

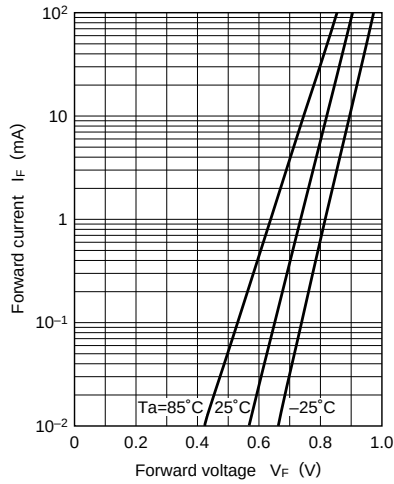
Parameter	Symbol	Condition	min	typ	max	Unit
Reverse current (DC)	I_R	$V_R= 33V$		0.01	100	nA
Forward voltage (DC)	V_F	$I_F=100mA$		0.96	1.1	V
Diode capacitance	C_D	$V_R= 6V, f=1MHz$		0.9	1.2	pF
Forward dynamic resistance	r_f^*	$I_F= 2mA, f=100MHz$		1.0	1.3	Ω

Note 1 : Rated input/output frequency : 100MHz
2 : * r_f measurement device : YHP MODEL 4191A RF IMPEDANCE ANALYZER

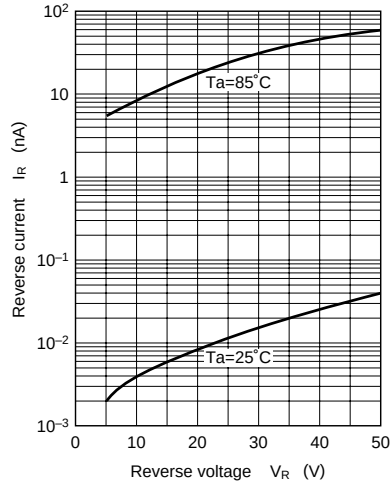
■ Marking



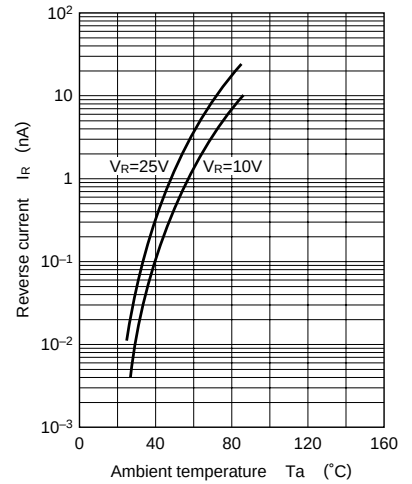
$I_F - V_F$



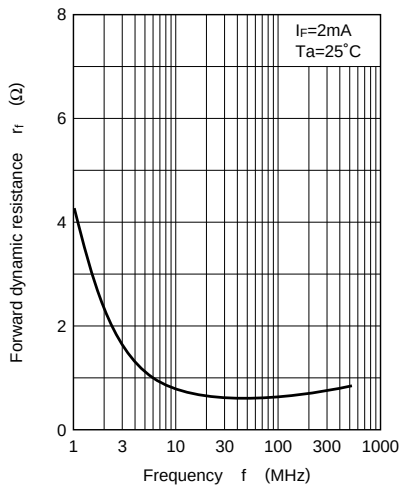
$I_R - V_R$



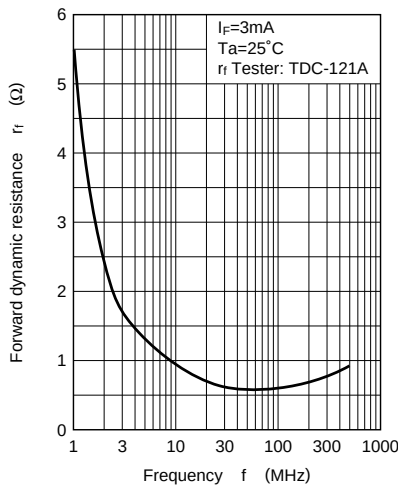
$I_R - T_a$



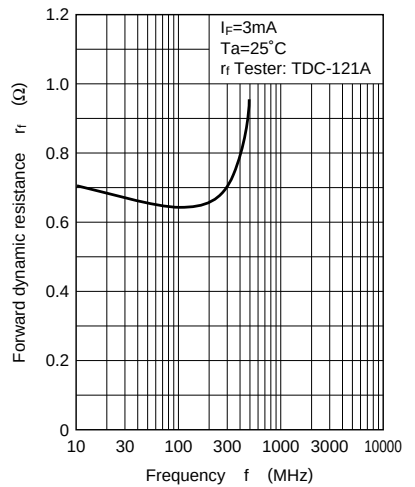
$r_f - f$



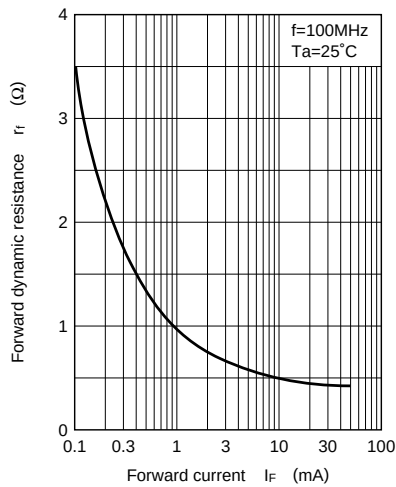
$r_f - f$



$r_f - f$



$r_f - I_F$



$C_D - V_R$

